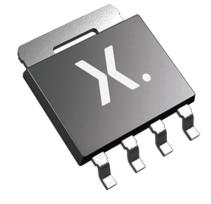


BUK7Y153-100EX Datasheet

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DiGi Electronics Part Number
Manufacturer
Manufacturer Product Number
Description
Detailed Description

BUK7Y153-100EX-DG Nexperia USA Inc. BUK7Y153-100EX MOSFET N-CH 100V 9.4A LFPAK56

N-Channel 100 V 9.4A (Tc) 37.3W (Tc) Surface Moun t LFPAK56, Power-SO8

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Purchase and inquiry

Manufacturer:
Nexperia USA Inc.
Product Status:
Active
Technology:
MOSFET (Metal Oxide)
Current - Continuous Drain (ld) @ 25°C:
9.4A (Tc)
Rds On (Max) @ ld, Vgs:
153mOhm @ 2A, 10V
Gate Charge (Qg) (Max) @ Vgs:
9.4 nC @ 10 V
Input Capacitance (Ciss) (Max) @ Vds:
497 pF @ 25 V
Power Dissipation (Max):
37.3W (Tc)
Grade:
Automotive
Mounting Type:
Surface Mount
Package / Case:
SC-100, SOT-669

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.29.0095	



BUK7Y153-100E

N-channel 100 V, 153 mΩ standard level MOSFET in LFPAK56 8 May 2013 Product data sheet

1. General description

Standard level N-channel MOSFET in an LFPAK56 (Power SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with V_{GS(th)} rating of greater than 1 V at 175 °C

3. Applications

- 12 V, 24 V and 48 V Automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

4. Quick reference data

Table 1. Qu	lick reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	100	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	9.4	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	37.3	W
Static charac	teristics	· · · · · · · · · · · · · · · · · · ·	1				
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I _D = 2 A; T _j = 25 °C; <u>Fig. 11</u>		-	104	153	mΩ
Dynamic cha	racteristics	· · · · · · · · · · · · · · · · · · ·					
Q _{GD}	gate-drain charge	V _{GS} = 10 V; I _D = 2 A; V _{DS} = 80 V; T _j = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>		-	3.8	-	nC

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BUK7Y153-100E

N-channel 100 V, 153 m Ω standard level MOSFET in LFPAK56

5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source		
3	S	source	a	G-UFT4
4	G	gate	ប្រុប្បុ	mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

6. Ordering information

Table 3. Ordering in	formation			
Type number	Type number Package			
	Name	Description	Version	
BUK7Y153-100E	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669	

7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK7Y153-100E	715310E

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Мах	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	100	V
V _{DGR}	drain-gate voltage	R _{GS} = 20 kΩ	-	100	V
V _{GS}	gate-source voltage	T _j ≤ 175 °C; DC	-20	20	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 1</u>	-	9.4	А
		T _{mb} = 100 °C; V _{GS} = 10 V; <u>Fig. 1</u>	-	6.7	А
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \ \mu$ s; Fig. 4	-	37.5	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>	-	37.3	W
T _{stg}	storage temperature		-55	175	°C

BUK7Y153-100E

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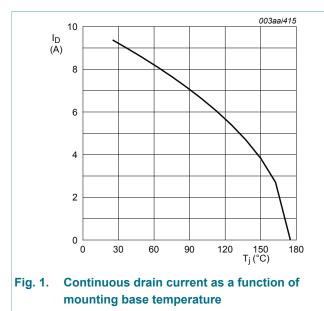
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N-channel 100 V, 153 m Ω standard level MOSFET in LFPAK56

Symbol	Parameter	Conditions		Min	Max	Unit
Tj	junction temperature			-55	175	°C
Source-drain	diode	-	1		1	
I _S	source current	T _{mb} = 25 °C		-	9.4	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	37.5	А
Avalanche ru	uggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\label{eq:ID} \begin{split} I_D &= 9.4 \; \text{A}; \; V_{sup} \leq 100 \; \text{V}; \; \text{R}_{GS} = 50 \; \Omega; \\ V_{GS} &= 10 \; \text{V}; \; \text{T}_{j(init)} = 25 \; ^{\circ}\text{C}; \; \text{unclamped}; \\ \hline \text{Fig. 3} \end{split}$	[1][2]	-	9.5	mJ

[1] Single-pulse avalanche rating limited by maximum junction temperature of 175 $^\circ\text{C}.$

[2] Refer to application note AN10273 for further information.



 $V_{GS} \ge 10V$

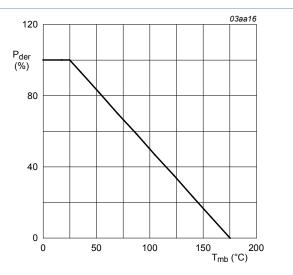
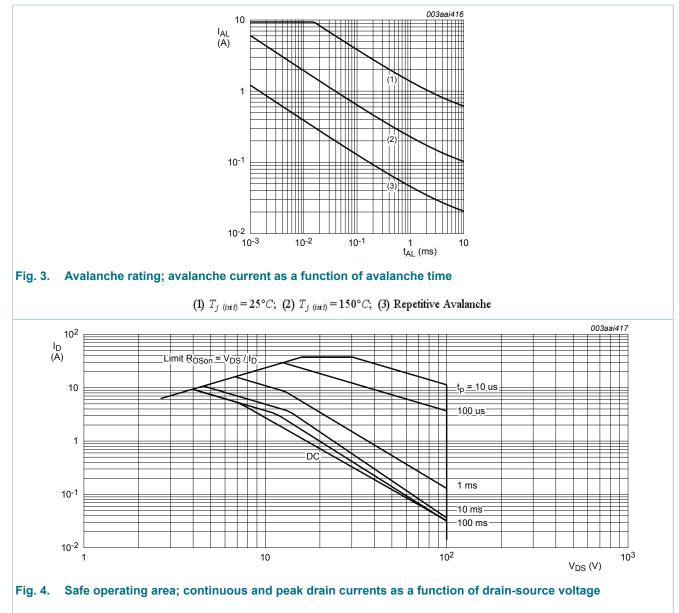


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

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N-channel 100 V, 153 m Ω standard level MOSFET in LFPAK56



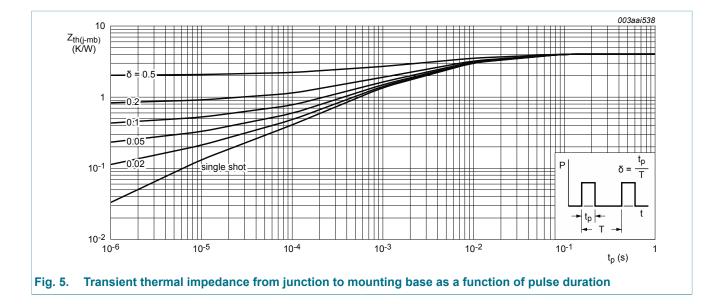
 $T_{mb} = 25^{\circ}C; \ I_{DM}$ is a single pulse

9. Thermal characteristics

Table 6. The	rmal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	-	4.03	K/W

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N-channel 100 V, 153 m Ω standard level MOSFET in LFPAK56



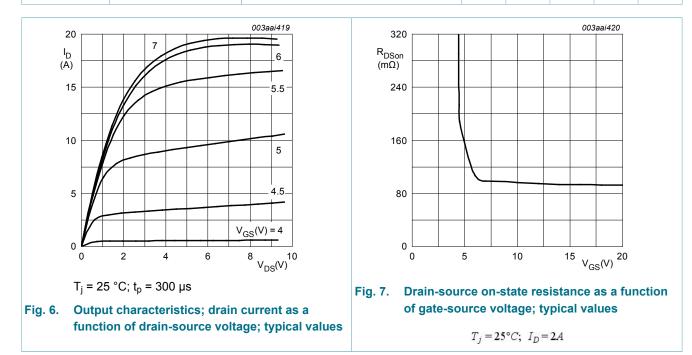
10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	100	-	-	V
	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C	90	-	-	V
V _{GS(th)}	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; Fig. 9; Fig. 10	2.4	3	4	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = -55 °C; Fig. 9	-	-	4.5	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 9	1	-	-	V
I _{DSS}	drain leakage current	V_{DS} = 100 V; V_{GS} = 0 V; T_j = 25 °C	-	0.07	1	μA
		V_{DS} = 100 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	μA
I _{GSS}	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 10 V; I _D = 2 A; T _j = 25 °C; <u>Fig. 11</u>	-	104	153	mΩ
	resistance	V _{GS} = 10 V; I _D = 2 A; T _j = 175 °C; Fig. 11; Fig. 12	-	-	424	mΩ
Dynamic ch	naracteristics					
Q _{G(tot)}	total gate charge	I_D = 2 A; V_{DS} = 80 V; V_{GS} = 10 V;	-	9.4	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C; <u>Fig. 13; Fig. 14</u>	-	1.5	-	nC
Q _{GD}	gate-drain charge		-	3.8	-	nC

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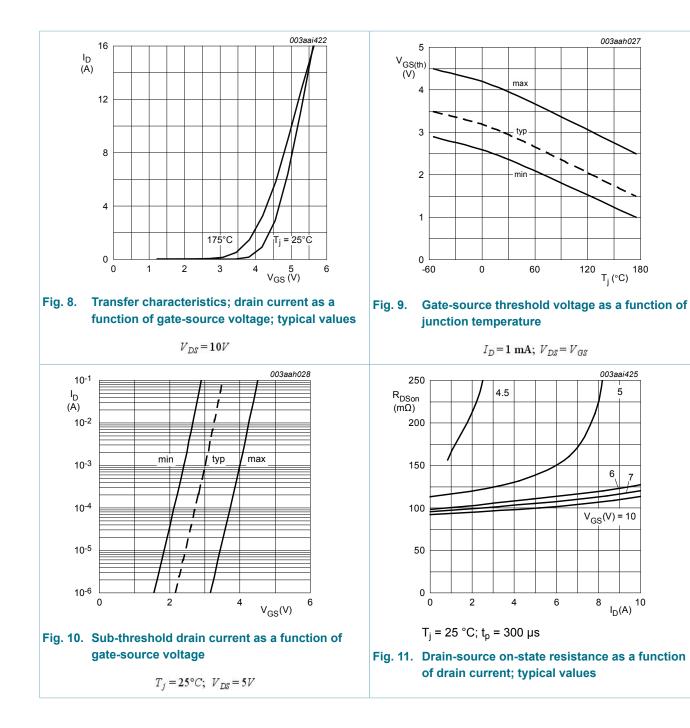
N-channel 100 V, 153 m Ω standard level MOSFET in LFPAK56

Symbol	Parameter	Conditions	М	in	Тур	Max	Unit
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz; T _j = 25 °C; <u>Fig. 15</u>	-		373	497	pF
C _{oss}	output capacitance		-		62	74	pF
C _{rss}	reverse transfer capacitance		-		49	67	pF
t _{d(on)}	turn-on delay time	V_{DS} = 80 V; R_{L} = 10 Ω ; V_{GS} = 10 V; $R_{G(ext)}$ = 5 Ω ; T_{j} = 25 °C	-		4	-	ns
t _r	rise time		-		4.8	-	ns
t _{d(off)}	turn-off delay time		-		7.8	-	ns
t _f	fall time	-	-		4.5	-	ns
Source-dra	ain diode	1	1 1				
V _{SD}	source-drain voltage	I_{S} = 2 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 16</u>	-		0.81	1.2	V
t _{rr}	reverse recovery time	$I_{S} = 2 \text{ A}; \text{ d}I_{S}/\text{d}t = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$	-		26.5	-	ns
Q _r	recovered charge	V _{DS} = 25 V; T _j = 25 °C	-		27.8	-	nC



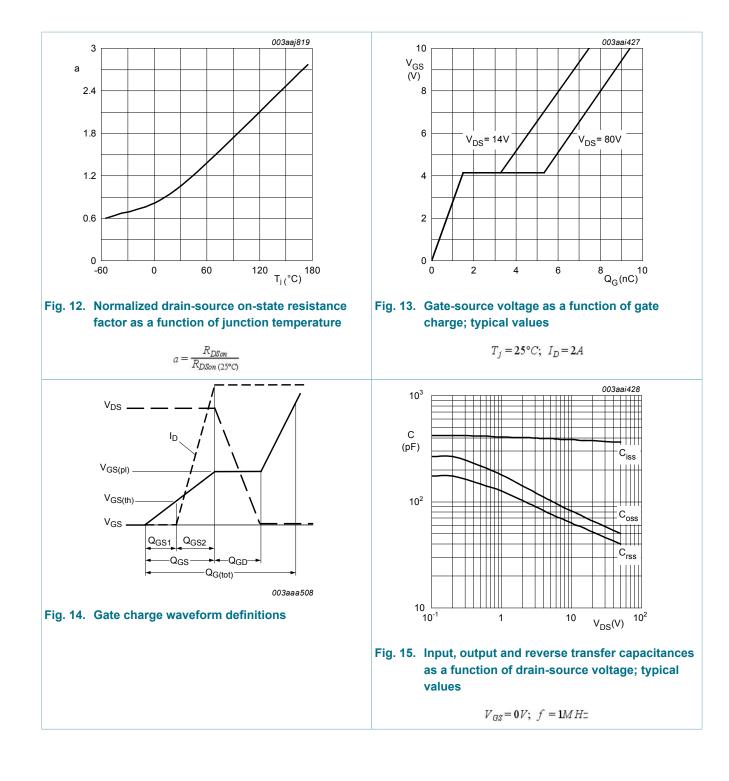
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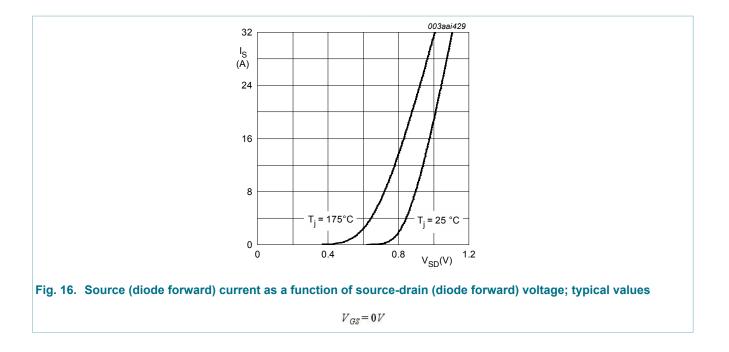
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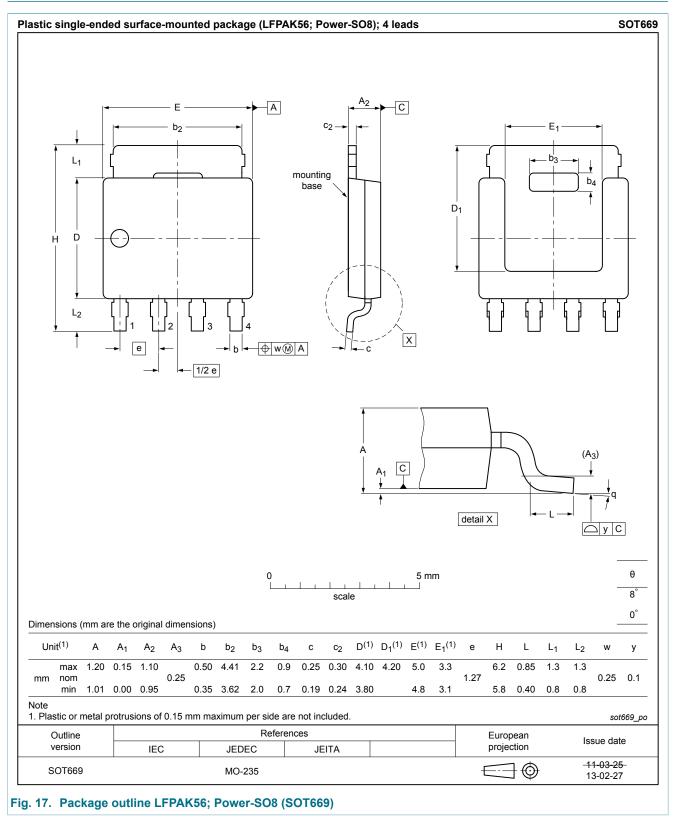
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11. Package outline



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N-channel 100 V, 153 mΩ standard level MOSFET in LFPAK56

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Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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N-channel 100 V, 153 mΩ standard level MOSFET in LFPAK56

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